

TENTATIVE TOSHIBA HYBRID DIGITAL INTEGRATED CIRCUIT
33,554,432-WORD BY 72-BIT SYNCHRONOUS DRAM MODULE
DESCRIPTION

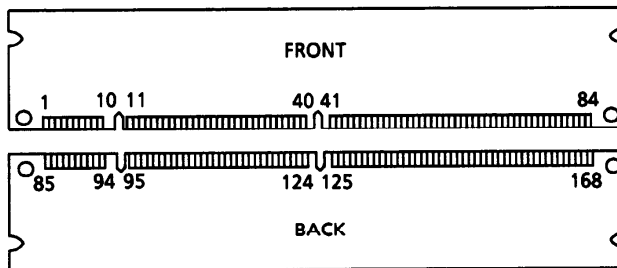
The THMY7232G1EG is a 33,554,432-word by 72-bit synchronous dynamic RAM module consisting of 18 TC59SM708FT DRAMs and an unbuffer on a printed circuit board.

FEATURES

- 33,554,432-word by 72-bit (double-bank) organization
- Single power supply of 3.3 V ± 0.3 V
- Pipeline architecture
- Auto-Refresh and Self-Refresh capability
- All inputs and outputs LVTTTL-compatible
- 4096 Refresh cycles per 64 ms
- Package: 168-pin DIMM (gold contacts)
- Based on Intel PC100 Rev. 1.0

	-80
t _{CK} Clock Cycle Time (CL = 2)	10 ns
t _{RAS} Active-to-Precharge Command Period (min)	48 ns
t _{AC} Access Time from CLK (CL = 2)	6 ns
t _{RC} Ref/Active-to-Ref/Active Command Period (min)	68 ns

PIN ASSIGNMENT (TOP VIEW)



PIN NAMES

A0 ~ A11	Address Inputs
BA0, BA1	Bank Select
DQ0 ~ DQ63	Data Inputs/Outputs
CB0 ~ CB7	Check Bits
/CS0 ~ /CS3	Chip Select
/RAS	Row Address Strobe
/CAS	Column Address Strobe
/WE	Write Enable
DQMB0 ~ DQMB7	Output Disable/Write Mask
CLK0 ~ CLK3	Clock Input
CKE0, CKE1	Clock Enable
SDA	Serial Data/Address for PD
SCL	Clock for PD
SA0 ~ SA2	Address for PD
VDD	Power (+3.3 V)
VSS	Ground
NC	No Connection

1	VSS	85	VSS	29	DOMB1	113	DOMB5	57	DO18	141	DO50
2	DO0	86	DO32	30	/CS0	114	/CS1	58	DO19	142	DO51
3	DO1	87	DO33	31	NC	115	/RAS	59	VDD	143	VDD
4	DO2	88	DO34	32	VSS	116	VSS	60	DO20	144	DO52
5	DO3	89	DO35	33	A0	117	A1	61	NC	145	NC
6	VDD	90	VDD	34	A2	118	A3	62	NC	146	NC
7	DO4	91	DO36	35	A4	119	A5	63	CKE1	147	NC
8	DO5	92	DO37	36	A6	120	A7	64	VSS	148	VSS
9	DO6	93	DO38	37	A8	121	A9	65	DO21	149	DO53
10	DO7	94	DO39	38	A10	122	BA0	66	DO22	150	DO54
11	DO8	95	DO40	39	BA1	123	A11	67	DO23	151	DO55
12	VSS	96	VSS	40	VDD	124	VDD	68	VSS	152	VSS
13	DO9	97	DO41	41	VDD	125	CLK1	69	DO24	153	DO56
14	DO10	98	DO42	42	CLK0	126	NC	70	DO25	154	DO57
15	DO11	99	DO43	43	VSS	127	VSS	71	DO26	155	DO58
16	DO12	100	DO44	44	NC	128	CKE0	72	DO27	156	DO59
17	DO13	101	DO45	45	/CS2	129	/CS3	73	VDD	157	VDD
18	VDD	102	VDD	46	DOMB2	130	DOMB6	74	DO28	158	DO60
19	DO14	103	DO46	47	DOMB3	131	DOMB7	75	DO29	159	DO61
20	DO15	104	DO47	48	NC	132	NC	76	DO30	160	DO62
21	CB0	105	CB4	49	VDD	133	VDD	77	DO31	161	DO63
22	CB1	106	CB5	50	NC	134	NC	78	VSS	162	VSS
23	VSS	107	VSS	51	NC	135	NC	79	CLK2	163	CLK3
24	NC	108	NC	52	CB2	136	CB6	80	NC	164	NC
25	NC	109	NC	53	CB3	137	CB7	81	NC (WP)	165	SA0
26	VDD	110	VDD	54	VSS	138	VSS	82	SDA	166	SA1
27	/WE	111	/CAS	55	DO16	139	DO48	83	SCL	167	SA2
28	DOMB0	112	DOMB4	56	DO17	140	DO49	84	VDD	168	VDD

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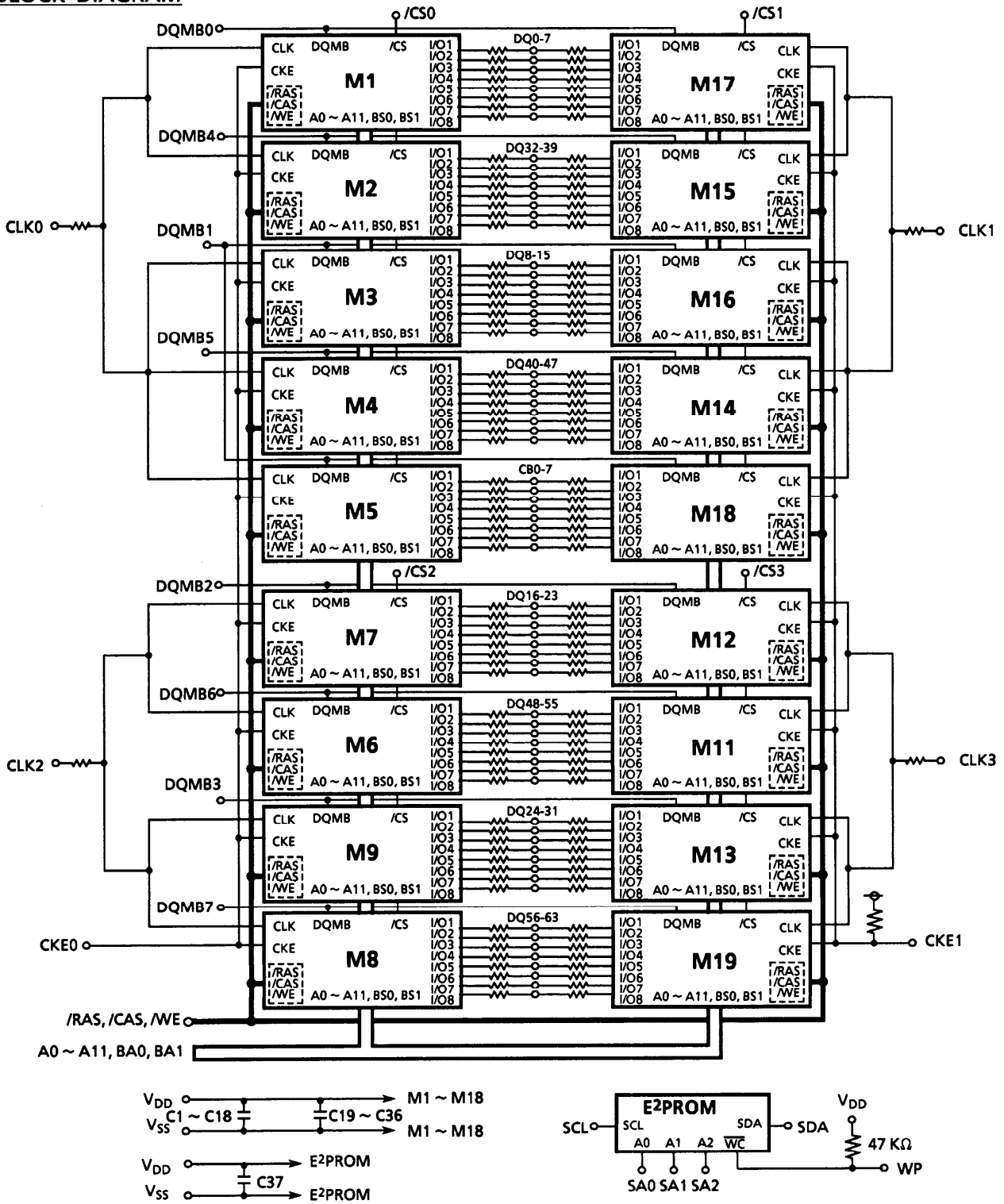
SERIAL PRESENCE DETECT (REV. 1.2A)

Byte Number	Function	Entry Value	Entry
0	Defines # of Bytes of information Written into Serial Memory by Module Manufacturer Group	128 Bytes	80h
1	Total # of Bytes in SPD Memory Device	256 Bytes	08h
2	Fundamental Memory Type (FPM, EDO, SDRAM...) from Appendix A	SDRAM	04h
3	# of Row Addresses on this Assembly	RA0 ~ RA11	0Ch
4	# of Column Addresses on this Assembly	CA0 ~ CA9	0Ah
5	# of Module Banks on this Assembly	2 Bank	02h
6	Data Width of this Assembly...	x72	48h
7	...Data Width Continuation	x72	00h
8	Voltage Interface Standard for this Assembly	LVTTL	01h
9	SDRAM Cycle Time at Max. Supported CAS Latency (CL), @ CL = X	CL = 3, 8.0 ns	80h
10	SDRAM Access from Clock @ CL = X	CL = 3, 6.0 ns	60h
11	DIMM Configuration Type (Non-parity, Parity, ECC)	ECC	02h
12	Refresh Rate/Type	15.625 μ s/Self-Refresh	80h
13	SDRAM Width, Primary DRAM	x8	08h
14	Error Checking SDRAM Data Width	x8	08h
15	Minimum Clock Delay, Back-to-Back Random Column Addresses	1 CLK	01h
16	Burst Lengths Supported	1, 2, 4, 8, Full page	8Fh
17	# of Banks on Each SDRAM Device	4 Banks	04h
18	CAS # Latencies Supported	2, 3	06h
19	CS # Latency		01h
20	WE # Latency		01h
21	SDRAM Module Attributes		00h
22	SDRAM Device Attributes: General		0Eh
23	Minimum Clock Cycle Time @ CL- X-1	CL = 2, 10 ns	A0h
24	Maximum Data Access Time from Clock @ CL X-1	CL = 2, 6.0 ns	60h
25	Minimum Clock Cycle Time @ CL X-2		00h
26	Maximum Data Access Time from Clock @ CL X-2		00h
27	Minimum Row Precharge Time	20 ns	14h
28	Minimum Row-Active-to-Row-Active Delay	20 ns	14h
29	Minimum RAS-to-CAS Delay	20 ns	14h
30	Minimum RAS Pulse Width	48 ns	30h
31	Module/Bank Density	128 MB	20h
32	CMD & Add Input Set-up time	2 ns	20h
33	CMD & Add Input Hold time	1 ns	10h
34	Data Input Set-up time	2 ns	20h
35	Data Input Hold time	1 ns	10h
36-61	Superset Information (may be used in future)		FFh
62	SPD Revision	Rev. 1.2A	12h
63	Check sum for Bytes 0 ~ 62	1EEDh	EDh

OPTIONAL

64	Manufacturers JEDEC ID Code (JEP-106E)		
65-71			
72	Place of Manufacture		
73-90	Manufacturer's Part Number		
91-92	Revision Code		
93-94	Date of Manufacture		
95-98	Assembly Serial Number		
99-125	Manufacturer-Specific Data		
126	Reserved	Intel Specification	64h
127	Reserved	Intel Specification	F7h
128-255			

BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS

SYMBOL	ITEM	RATING	UNIT	NOTES
V _{IN}	Input Voltage	-0.3 ~ V _{DD} + 0.3	V	1
V _{OUT}	Output Voltage	-0.3 ~ V _{DD} + 0.3	V	1
V _{DD}	Power Supply Voltage	-0.3 ~ 4.6	V	1
T _{OPR}	Operating Temperature	0 ~ 70	°C	1
T _{STG}	Storage Temperature	-55 ~ 125	°C	1
P _D	Power Dissipation	18	W	1
I _{OUT}	Short-Circuit Output Current	50	mA	1

RECOMMENDED DC OPERATING CONDITIONS (Ta = 0° ~ 70°C)

SYMBOL	PARAMETER	MIN	TYP.	MAX	UNIT	NOTES
V _{DD}	Supply Voltage	3.0	3.3	3.6	V	2
V _{IH}	LVTTL Input High Voltage	2.0	-	V _{DD} + 0.3	V	2
V _{IL}	LVTTL Input Low Voltage	-0.3	-	0.8	V	2

CAPACITANCE (V_{CC} = 3.3 V, f = 1 MHz, Ta = 0° ~ 70°C)

SYMBOL	PARAMETER	MIN	MAX	UNIT
C ₁	Input Capacitance (A0 ~ A11)	-	TBD	pF
C ₂	Input Capacitance ($\overline{\text{RAS}}$, $\overline{\text{CAS}}$, $\overline{\text{WE}}$, BA0, BA1)	-	TBD	pF
C ₃	Input Capacitance (CLK0 ~ CLK3)	-	TBD	pF
C ₄	Input Capacitance ($\overline{\text{CS0}}$ ~ $\overline{\text{CS3}}$)	-	TBD	pF
C ₅	Input Capacitance (DQMB0 ~ DQMB7)	-	TBD	pF
C _{DQ}	I/O Capacitance (DQ0 ~ DQ63, CB0 ~ CB7)	-	TBD	pF

DC CHARACTERISTICS ($V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$, $T_a = 0^\circ \sim 70^\circ\text{C}$)

SYMBOL	ITEM	MIN	MAX	UNIT	NOTES	
I_{CC1}	OPERATING CURRENT Active-Precharge Command Cycling without Burst Operation ($t_{CK} = \text{min}$, $t_{RC} = \text{min}$)	1-Bank Operation	-	1080	mA	3, 5
I_{CC2}	STANDBY CURRENT ($t_{CK} = \text{min}$, $\overline{CS} = V_{IH}$, $V_{IH/L} = V_{IH}(\text{min}) / V_{IL}(\text{max})$ Bank: Inactive State)	CKE = V_{IH}	-	720	mA	3
I_{CC2P}		CKE = V_{IL} (Power-Down Mode)	-	18		
I_{CC2S}	STANDBY CURRENT (CLK = V_{IL} , $\overline{CS} = V_{IH}$, $V_{IH/L} = V_{IH}(\text{min}) / V_{IL}(\text{max})$ Bank: Inactive State)	CKE = V_{IH}	-	180	mA	
I_{CC2PS}		CKE = V_{IL} (Power-Down Mode)	-	18		
I_{CC3}	NO OPERATING CURRENT ($t_{CK} = \text{min}$, $\overline{CS} = V_{IH}(\text{min})$ Bank: Active State (2 banks))	CKE = V_{IH}	-	810	mA	3, 5
I_{CC3P}		CKE = V_{IL} (Power-Down Mode)	-	180	mA	3
I_{CC4}	BURST OPERATING CURRENT ($t_{CK} = \text{min}$, $\overline{CS} = V_{IH}(\text{min})$, Read / Write Command Cycling)		-	1350	mA	3, 4, 5
I_{CC5}	AUTO-REFRESH CURRENT ($t_{CK} = \text{min}$, Auto-Refresh Command Cycling)		-	3240	mA	3, 5
I_{CC6}	SELF-REFRESH CURRENT (Self-Refresh Mode, CKE = 0.2 V)		-	18	mA	3
$I_{I(L)}$	INPUT LEAKAGE CURRENT ($0\text{ V} \leq V_{IN} \leq V_{DD}$, All Other Pins Not under Test = 0 V)		-5	5	μA	
$I_{O(L)}$	OUTPUT LEAKAGE CURRENT (D_{OUT} Is Disabled, $0\text{ V} \leq V_{OUT} \leq V_{DD}$)		-5	5	μA	
V_{OH}	OUTPUT LEVEL LVTTTL Output H-Level Voltage ($I_{OUT} = -2\text{ mA}$)		2.4	-	V	
V_{OL}	OUTPUT LEVEL LVTTTL Output L-Level Voltage ($I_{OUT} = 2\text{ mA}$)		-	0.4	V	

AC CHARACTERISTICS AND OPERATING CONDITIONS

(V_{CC} = 3.3 V ± 0.3 V, T_a = 0° ~ 70°C) (Notes 6, 7, 11)

SYMBOL	PARAMETER	MIN	MAX	UNIT	NOTES		
t _{RC}	Ref/Active-Ref/Active Command Period	68		ns	9		
t _{RAS}	Active- Precharge Command Period	48	100000				
t _{RCD}	Active-Read/Write Command Delay Time	20					
t _{CCD}	Read/Write(a) -Read/Write(b) Command Period	1		cycle			
t _{RP}	Precharge-Active Command Period	20		ns			
t _{RRD}	Active(a)-Active(b) Command Period	20					
t _{WR}	Write Recovery Time	CL* = 2	10				
		CL* = 3	8				
t _{CK}	CLK Cycle Time	CL* = 2	10			1000	
		CL* = 3	8			1000	
t _{CH}	CLK High-Level Width	3					10
t _{CL}	CLK Low-Level Width	3					
t _{AC}	Access Time from CLK	CL* = 2				6	
		CL* = 3				6	
t _{OH}	Output Data Hold Time	3					
t _{HZ}	Output Data High-Impedance Time	3	8				8
t _{LZ}	Output Data Low-Impedance Time	0					
t _{SB}	Power-Down Mode Entry Time	0	8				
t _T	Transition Time of CLK (Rise and Fall)	0.5	10				
t _{DS}	Data-In Set-up Time	2					
t _{DH}	Data-In Hold Time	1					
t _{AS}	Address Set-up Time	2					
t _{AH}	Address Hold Time	1					
t _{CKS}	CKE Set-up Time	2					
t _{CKH}	CKE Hold Time	1					
t _{CMS}	Command Set-up Time	2					
t _{CMH}	Command Hold Time	1					
t _{REF}	Refresh Time		64	ms			
t _{RSC}	Mode Register Set Cycle Time	16		ns	9		

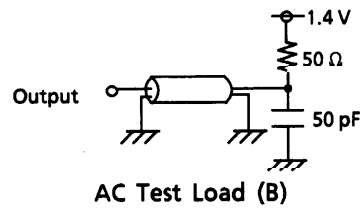
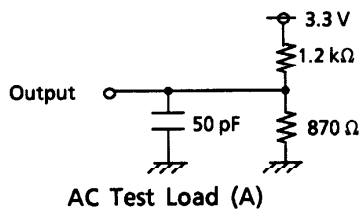
* CL is \overline{CAS} latency.

NOTES:

1. Conditions outside the limits listed under Absolute Maximum Ratings may cause permanent damage to the device.
2. All voltages are referenced to Vss.
3. These parameters depend on the cycle rate and their values are measured at the cycle rate obtained using the minimum values of t_{CK} and t_{RC}. Input signals are changed once during t_{CK}.
4. These parameters depend on the output loading. The specified values are obtained with the output open.
5. These values are measured under the following conditions.
 Front (or back): Under the measuring conditions given on the data sheet
 Back (or front): In standby (measured under the I_{CC2} conditions)

6. AC TEST CONDITIONS

Reference Level for Output Signals	1.4 V / 1.4 V
Output Load	See the diagram for AC Test Load (B) below
Input Signal Levels	2.4 V / 0.4 V
Transition Time (Rise and Fall) of Input Signals	2 ns
Reference Level of Input Signals	1.4 V



7. Transition times are measured between the V_{IH} and V_{IL} levels. The transition (rise and fall) of input signals has a fixed slope.
8. t_{HZ} defines the time at which the outputs go open-circuit and are not reference levels.

9. These parameters are specified for a given number of clock cycles and a given operating frequency. The relationship between the number of clock cycles, the timing value and the frequency (a clock period) is as follows:

$$\text{number of clock cycles} = \text{specified timing value} / \text{clock period}$$

(Fractions are rounded up to a whole number.)

10. t_{CH} is the pulse width of CLK measured from the positive edge to the negative edge and referenced to V_{IH} (min). t_{CL} is the pulse width of CLK measured from the negative edge to the positive edge and referenced to V_{IL} (max).

11. Power-up Sequence

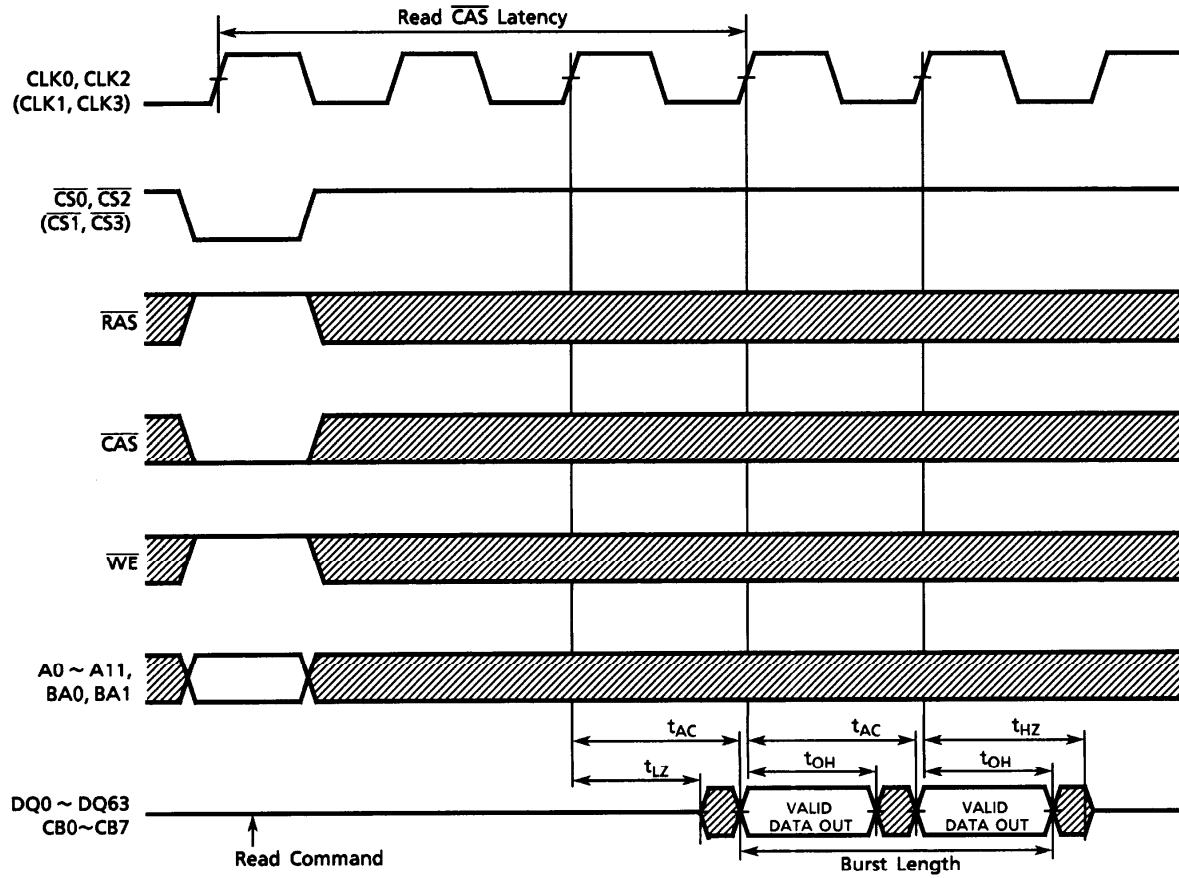
Power-up must be performed in the following sequence.

- 1) Power must be applied to V_{DD} with all input signals held in the NOP state. The CLK signal must be started at the same time as power is applied.
- 2) After power-up a pause of at least 200 μ seconds is required. Then, DQMB and CKE must be held High (at the V_{DD} level) to ensure that the DQ and CB outputs are High-Impedance.
- 3) Both banks must be precharged.
- 4) The Mode Register Set command must be asserted to initialize the Mode Register.
- 5) An Auto-Refresh operation, consisting of at least eight Auto-Refresh cycles, must be performed.

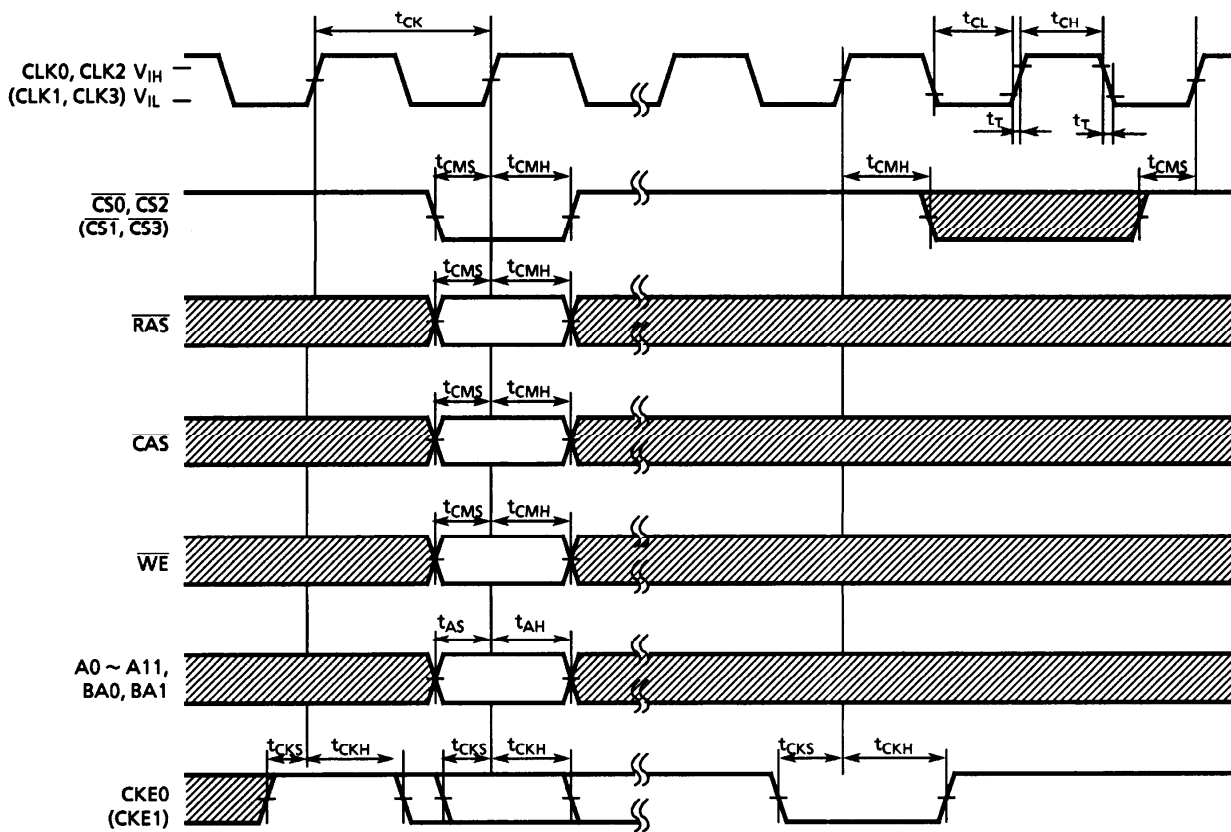
The order in which 4) and 5) are performed is interchangeable.

TIMING DIAGRAMS

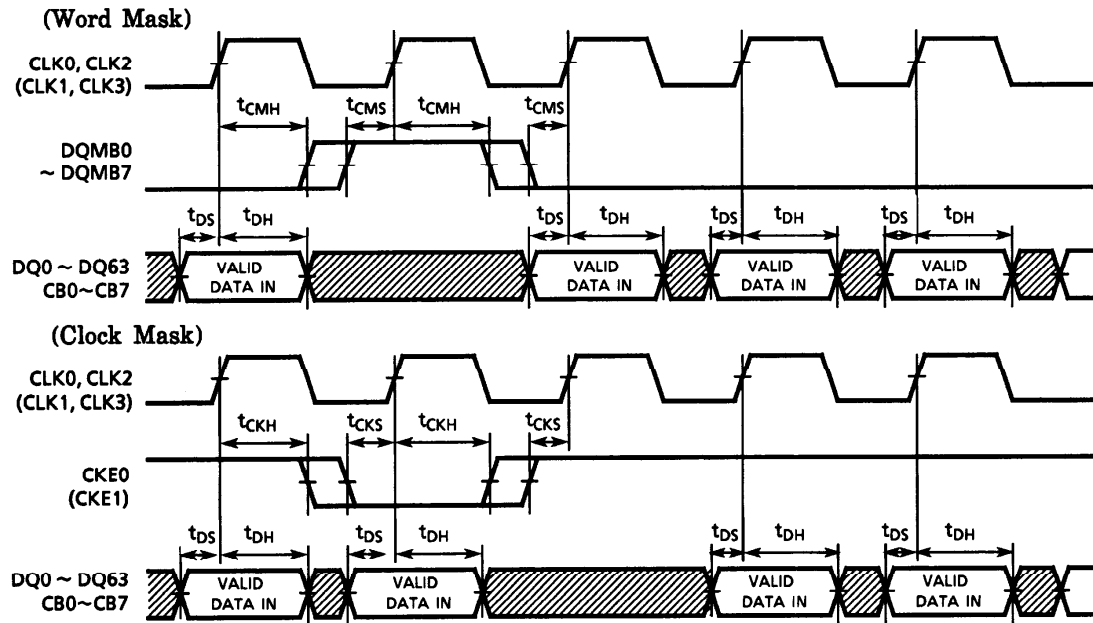
READ TIMING



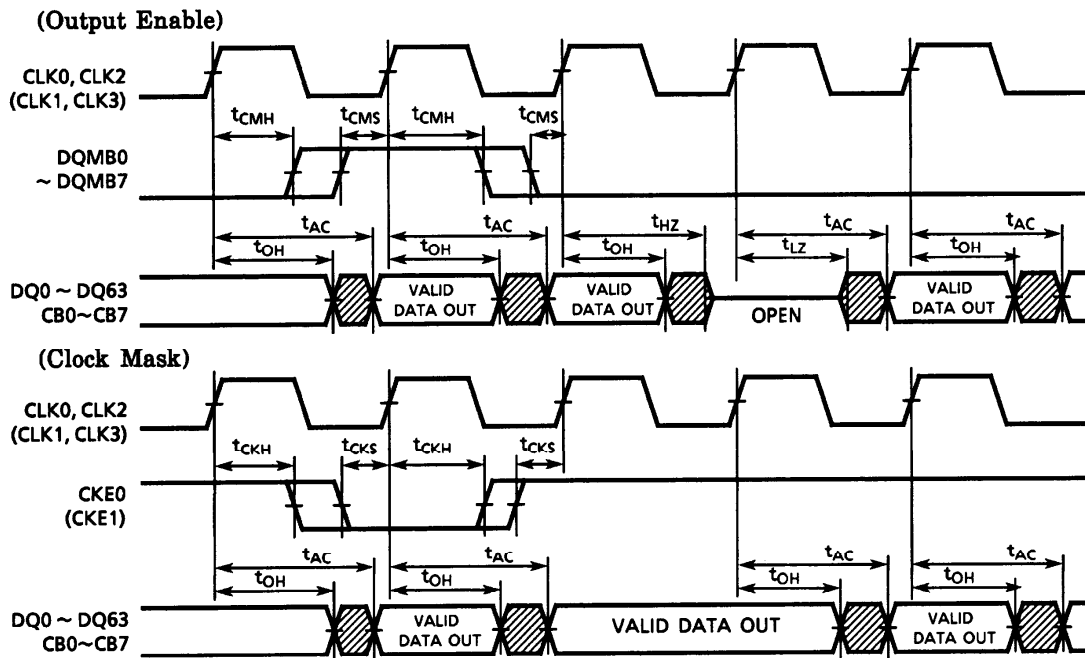
COMMAND INPUT TIMING



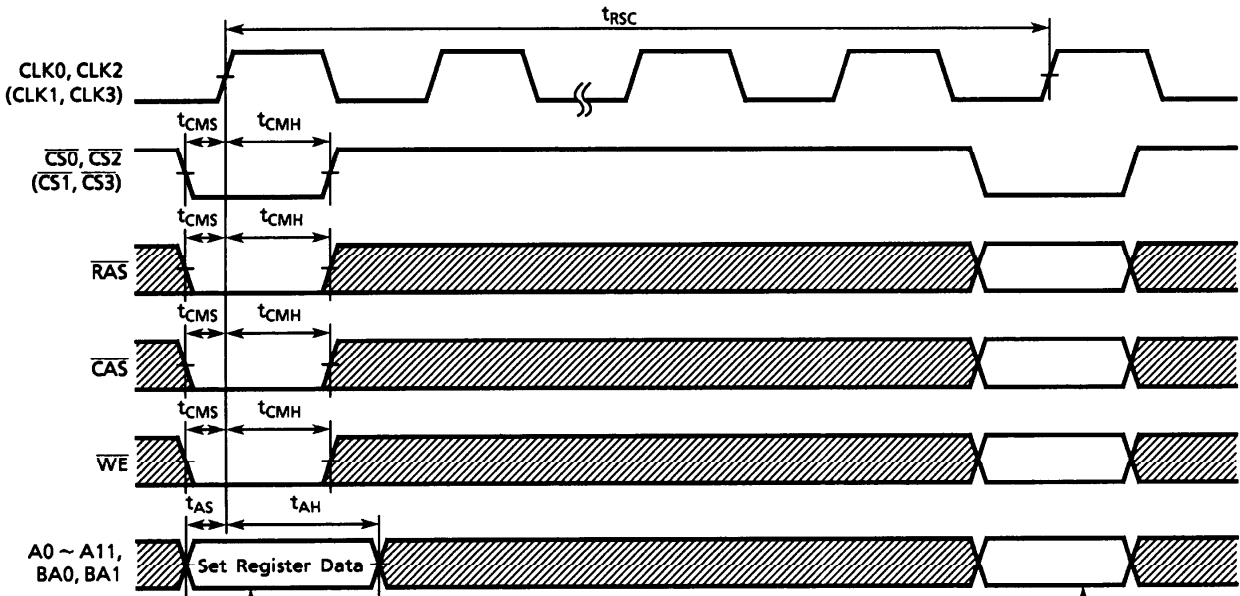
CONTROL TIMING FOR INPUT DATA



CONTROL TIMING FOR OUTPUT DATA



MODE REGISTER SET CYCLE



A0	Burst Length	
A1	Burst Length	
A2	Burst Length	
A3	Addressing Mode	
A4	\overline{CAS} Latency	
A5	\overline{CAS} Latency	
A6	\overline{CAS} Latency	
A7	0	(Test Mode)
A8	0	Reserved
A9	Write Mode	
A10	0	Reserved
A11	0	
BA0	0	
BA1	0	

			Burst Length	
A2	A1	A0	Sequential	Interleaved
0	0	0	1	1
0	0	1	2	2
0	1	0	4	4
0	1	1	8	8
1	0	0	Reserved	Reserved
1	0	1		
1	1	0	Full Page	Reserved
1	1	1		

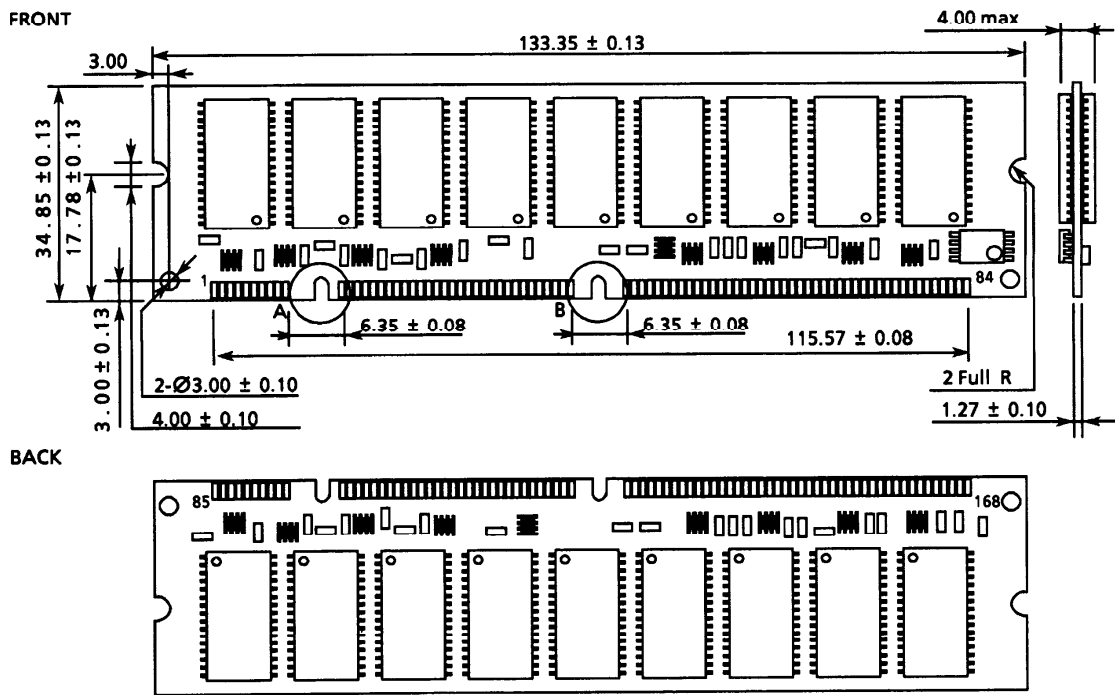
A3	Addressing Mode
0	Sequential
1	Interleaved

A6	A5	A4	\overline{CAS} Latency
0	0	0	Reserved
0	0	1	Reserved
0	1	0	2
0	1	1	3
1	0	0	Reserved

A9	Single Write Mode
0	Burst Read and Burst Write
1	Burst Read and Single Write

PACKAGE DIMENSIONS (THMY7232G1EG)

Unit: mm



CONTACT DIMENSIONS

A: Unbuffered keying

B: 3.3-V keying

